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X u	rgent 🗆 For Review	☐ Please Comment	☐ Please Reply	□ Please Recycle		
Re:	Hussein I. Hanafi et al. U.S. Patent Appln. No. 1 Docket: YOR920020182					
Phone	<b>1</b>	Date:	10/5/2005			
Fax	571-273-8300	Pages:	8 pages including fax cover			
To:	Art Unit 2823	From:	Leslie S. Szivos			

### PATENT OFFICE DATE STAMP WILL ACKNOWLEDGE RECEIPT OF:

- 1. Transmittal of Information Disclosure Statement (in duplicate)
- 2. Information Disclosure Statement (w/Form PTO-1449)
- 3. Certificate of transmission by facsimile dated October 5, 2005
- 5. Authorization to charge IBM deposit account

If you have any questions concerning this facsimile please contact Vivian Henriquez at 516-742-4343. Thank you

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### OCT 0 5 2005

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))					Docket No. YOR920020182US2					
In Re Application Of: Hussein L. Hanafi et al.										
Application No. Filing Date Examiner Customer No. Group Art Unit Confirm										
10/	659,949	September 11, 2003	Fernando L. Toledo	23389	2823	5877				
Title:	Title: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATION OXIDE REMOVAL ETCH									
	Address to:  Commissioner for Patents  P.O. Box 1450  Alexandria, VA 22313-1450									
			37 CFR 1.97(b)							
	1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.  37 CFR 1.97(c)									
2.	2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:									
	☐ the statement specified in 37 CFR 1.97(e);									
	OR									
	□ the f	ee set forth in 37 CF	R 1.17(p).							

## OCT 0 5 2005

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))						Docket No. YOR920020182US2			
In Re Application of: Hussein L Hanafi et al.									
Application No.	Examiner		Customer No.	Group Art Unit	Confirmation No.				
10/659,949	September 11, 2003	Fernando L. Toledo		23389	2823	5877			
Title: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATION OXIDE REMOVAL ETCH									
	Payment of Fee  (Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))  A check in the amount of is attached.  50/0510/IBM								
as describe □ Ch ☑ Cre	as described below.  Charge the amount of Credit any overpayment.								
WARNING	y credit card. Form P : Information on thi n this form. Provide	s form may become	public. C	redit card info authorization	rmation should on PTO-2038.	not be			
included on this form. Provide credit card information and authorization on PTO-2038.  Certificate of Transmission by Facsimile*  Certificate of Mailing by First Class Mail  Certificate of Mailing b									
Garden City, New Y	ork 11530								

OCT 0 5 2005

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))					Docket No. YOR920020182US2					
In Re A	In Re Application Of: Hussein L Hanafi et al.									
Application No. Filing Date Examiner Customer No. Group Art Unit Confirmation										
10/659,949 September 11, 2003 Fernando L. Toledo 23389 2823										
Title:	Title: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATION OXIDE REMOVAL ETCH									
			Address to: Commissioner for Patern P.O. Box 1450 Alexandria, VA 22313-14							
		•	37 CFR 1.97(b)							
1. 23	1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.									
			37 CFR 1.97(c)							
2.	The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:									
	☐ the s	statement specified in	37 CFR 1.97(e);		•					
		C	OR							
	the fee set forth in 37 CFR 1.17(p).									

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OCT 0 5 2005 TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT Docket No. (Under 37 CFR 1.97(b) or 1.97(c)) YOR920020182US2 In Re Application of: Hussein I. Hanafi et al. Application No. Filing Date Examiner Customer No. Group Art Unit Confirmation No. 10/659,949 September 11, 2003 Fernando L. Toledo 23389 5877 2823 LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATION OXIDE REMOVAL ETCH Payment of Fee (Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p)) A check in the amount of is attached. 50/0510/IBM The Director is hereby authorized to charge and credit Deposit Account No. as described below. Charge the amount of X Credit any overpayment. X Charge any additional fee required. ☐ Payment by credit card. Form PTO-2038 is attached. WARNING: Information on this form may become public. Credit card information should not be Included on this form. Provide credit card information and authorization on PTO-2038. Certificate of Transmission by Facsimile\* Certificate of Mailing by First Class Mail I certify that this document and authorization to charge deposit I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage account is being facsimile transmitted to the United States Patent and Trademark Office (Fax 571-273-8300) first class mail in an envelope addressed to \*Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 SER 1.8(a)] on October 5, 2005 (Date) (Date) Correspondence Leslie S. Szivos, Ph.D. Typed or Printed Name of Person Signing Optificate Typed or Printed Name of Person Mailing Certificate \*This certificate may deposit account. Dated: October 5, 2005 Signature Leslie S. Szivos, Ph.D. Registration No. 39,394 SCULLY, SCOTT, MURPHY & PRESSER 400 Garden City Plaza - Suite 300 Garden City, New York 11530

cc:

P10A/REV05

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Hussein I. Hanafi et al.

Examiner: Fernando L. Toledo

Serial No:

10/659,949

Art Unit: 2823

Dated: October 5, 2005

Filed:

September 11, 2003

**Docket:** YOR920020182US2 (15790A)

For: LOW RESISTANCE T-GATE MOSFET

DEVICE USING A DAMASCENE GATE

PROCESS AND AN INNOVATION

OXIDE REMOVAL ETCH

Confirmation No. 5877

Mailstop Amendment Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

#### INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. United States Patent 6,271,094 B1, dated August 7, 2001, issued to Boyd et al.

#### **CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on October 5, 2005

Dated: October 5, 2005

Leslie & Szivos, Ph.D.

Consideration of this Information Disclosure Statement is respectfully requested, since the art provided may be material to the examination of the present application as defined under 37 C.F.R. §1.56.

Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

Respectfully submitted,

Leslie S. Szivos

Registration No. 39,394

Scully, Scott, Murphy & Presser 400 Garden City Plaza – Suite 300 Garden City, New York 11530 (516) 742-4343

LSS:vh

				Docket Number (Optional) Application Number							
INFORMATION DISCLOSURE CITATION					YOR920020182US2 (15790A) 10/659,949						
	пиро	(Use several sheets if necess		Applicant(s) Hussein I. Hanafi et al.							
		( occus of necess	Filing Date Group Art Unit								
			September 11, 20	03	2	823					
			U.S	. PATENT	DOCUMENTS	•	•				
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME		CLASS	CLASS SUBCLASS		FILING DATE  EF APPROPRIATE		
		6,271,094 B1	8/7/2001	Boyd et	al.				KERTE		
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U.S. PATENT APPLICATION PUBLICATIONS											
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Form PTO-A820

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